

Advance Information

Silicon Controlled Rectifiers Reverse Blocking Thyristors

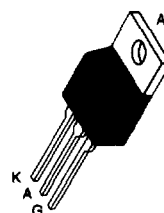
Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave, silicon gate-controlled devices are needed.

- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS
- High Surge Current Capability — 100 Amperes
- Industry Standard TO-220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity

MCR12 SERIES*

*Motorola preferred devices

SCRs
12 AMPERES RMS
400 thru 800
VOLTS



CASE 221A-06
(TO-220AB)
Style 3

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (1) Peak Repetitive Reverse Voltage ($T_J = -40$ to 125°C)	V_{DRM} V_{RRM}	400 600 800	Volts
On-State RMS Current (All Conduction Angles)	$I_T(\text{RMS})$	12	A
Peak Non-repetitive Surge Current (One Half Cycle, 60 Hz, $T_J = 125^\circ\text{C}$)	I_{TSM}	100	A
Circuit Fusing Consideration ($t = 8.3$ ms)	I^2t	41	A ² sec
Peak Gate Power (Pulse Width ≤ 1.0 μs , $T_C = 80^\circ\text{C}$)	P_{GM}	5.0	Watts
Average Gate Power ($t = 8.3$ ms, $T_C = 80^\circ\text{C}$)	$P_{G(AV)}$	0.5	Watts
Peak Gate Current (Pulse Width ≤ 1.0 μs , $T_C = 80^\circ\text{C}$)	I_{GM}	2.0	A
Operating Junction Temperature Range	T_J	-40 to $+125$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to $+150$	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.0 62.5	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	$^\circ\text{C}$

- (1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

This document contains information on a new product. Specifications and information herein are subject to change without notice.

Preferred devices are Motorola recommended choices for future use and best overall value.

MCR12 SERIES

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Forward Blocking Current $T_J = 25^\circ\text{C}$	I_{ORM}	—	—	0.01	mA
Peak Reverse Blocking Current $T_J = 125^\circ\text{C}$ ($V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}, \text{ Gate Open}$)	I_{RRM}	—	—	2.0	mA

ON CHARACTERISTICS

Peak On-State Voltage* ($I_{TM} = 24 \text{ A}$)	V_{TM}	—	—	2.2	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}, R_L = 100 \Omega$)	I_{GT}	2.0	7.0	20	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ V}, R_L = 100 \Omega$)	V_{GT}	0.5	0.65	1.0	Volts
Hold Current (Anode Voltage = 12 V)	I_H	4.0	25	40	mA

DYNAMIC CHARACTERISTICS

Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}, \text{ Exponential Waveform, Gate Open, } T_J = 25^\circ\text{C}$)	(dv/dt)	50	200	—	V/ μs
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*Indicates Pulse Test: Pulse Width $\leq 2.0 \text{ ms}$, Duty Cycle $\leq 2\%$.